

removing part of said additional material, removed part of said additional material being located on said patterned photoresist and said the substrate.

IN THE ABSTRACT:

The Abstract has been amended as follows:

A method for reducing line edge roughness of patterned photoresist, (at least )include at least: providing a patterned photoresist which (at least )has at least a trench and is located on a substrate; filling trenches so let that trenches are totally filled by an additional material, wherein the additional material is easily to bond with the patterned photoresist; removing part of the additional material which is located on patterned photoresist and the substrate; and treating the additional material so let that adhesion between the additional material and patterned photoresist is enhanced after the additional material is treated. Moreover, while only trenches are filled by the additional material, step of removing part of the additional material could be omitted; while adhesion between the additional material and patterned photoresist is good, step of treating the additional material could be omitted.